

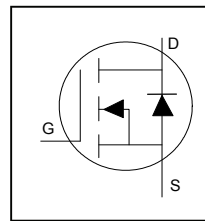
**Application**

- Brushed motor drive applications
- BLDC motor drive applications
- Battery powered circuits
- Half-bridge and full-bridge topologies
- Synchronous rectifier applications
- Resonant mode power supplies
- OR-ing and redundant power switches
- DC/DC and AC/DC converters
- DC/AC inverters

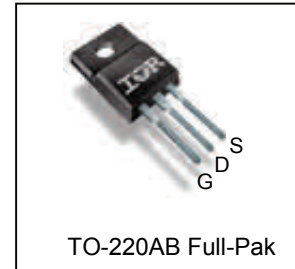
**Benefits**

- Improved gate, avalanche and dynamic dV/dt ruggedness
- Fully characterized capacitance and avalanche SOA
- Enhanced body diode dV/dt and dI/dt capability
- Lead-Free, RoHS compliant

HEXFET® Power MOSFET



<b>V<sub>DSS</sub></b>	<b>40V</b>
<b>R<sub>DS(on)</sub> typ.</b>	<b>2.6mΩ</b>
	<b>max</b>
<b>I<sub>D</sub></b>	<b>80A</b>



<b>G</b>	<b>D</b>	<b>S</b>
Gate	Drain	Source

Base part number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRFI7446GPbF	TO-220 Full-Pak	Tube	50	IRFI7446GPbF

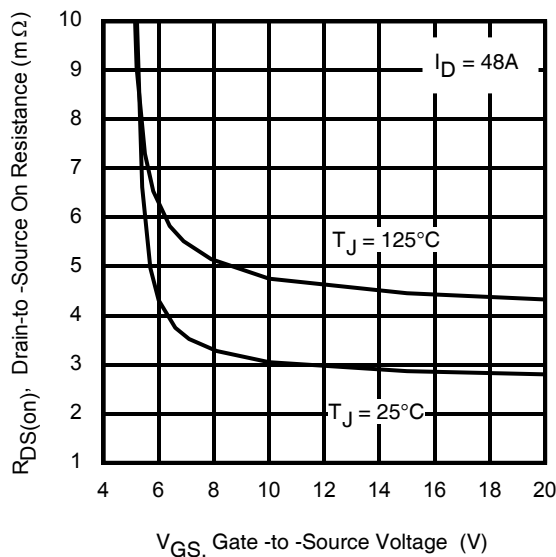


Fig 1. Typical On-Resistance vs. Gate Voltage

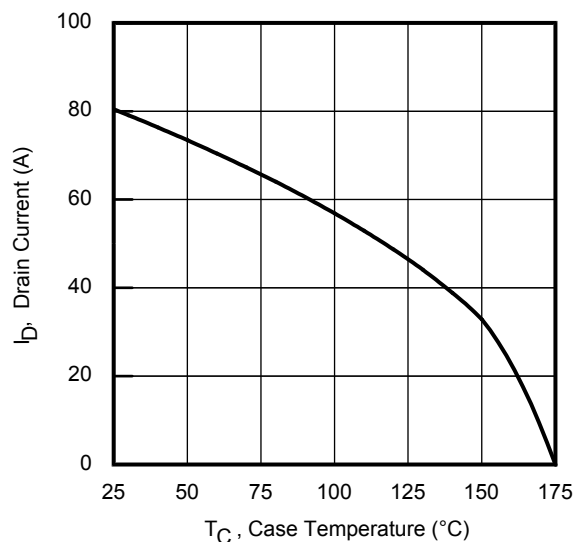


Fig 2. Maximum Drain Current vs. Case Temperature

**Absolute Maximum Rating**

Symbol	Parameter	Max.	Units
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	80	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	57	
$I_{DM}$	Pulsed Drain Current ①	320	
$P_D @ T_C = 25^\circ\text{C}$	Maximum Power Dissipation	40.5	W
	Linear Derating Factor	0.27	W/°C
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
$T_J$	Operating Junction and	-55 to + 175	°C
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 seconds (1.6mm from case)		
	Mounting Torque, 6-32 or M3 Screw	10 lbf·in (1.1 N·m)	

**Avalanche Characteristics**

$E_{AS}$ (Thermally limited)	Single Pulse Avalanche Energy ②	233	mJ
$E_{AS}$ (tested)	Single Pulse Avalanche Energy Tested Value ③	319	
$I_{AR}$	Avalanche Current ①	See Fig. 15, 16, 23a, 23b	A
$E_{AR}$	Repetitive Avalanche Energy ①		mJ

**Thermal Resistance**

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ⑦	—	3.7	°C/W
$R_{\theta JA}$	Junction-to-Ambient	—	65	

**Static @  $T_J = 25^\circ\text{C}$  (unless otherwise specified)**

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	40	—	—	V	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	38	—	mV/°C	Reference to $25^\circ\text{C}$ , $I_D = 1.0\text{mA}$ ①
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	2.6	3.3	mΩ	$V_{GS} = 10\text{V}, I_D = 48\text{A}$
$V_{GS(th)}$	Gate Threshold Voltage	2.2	3.0	3.9	V	$V_{DS} = V_{GS}, I_D = 100\mu\text{A}$
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	1.0	μA	$V_{DS} = 40\text{V}, V_{GS} = 0\text{V}$
		—	—	150		$V_{DS} = 40\text{V}, V_{GS} = 0\text{V}, T_J = 125^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20\text{V}$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20\text{V}$
$R_G$	Gate Resistance	—	1.3	—	Ω	

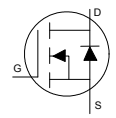
**Notes:**

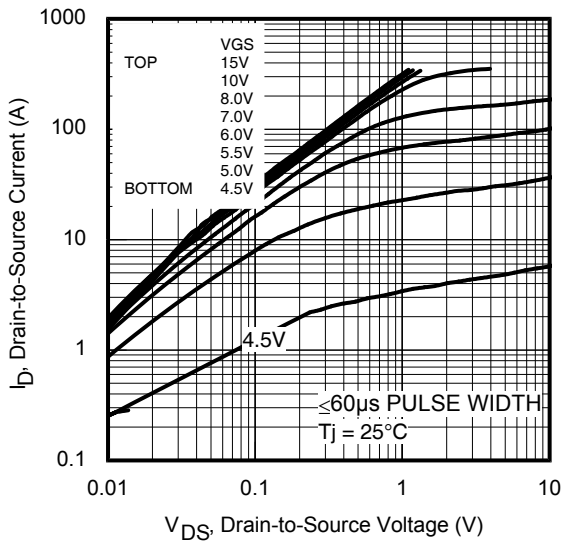
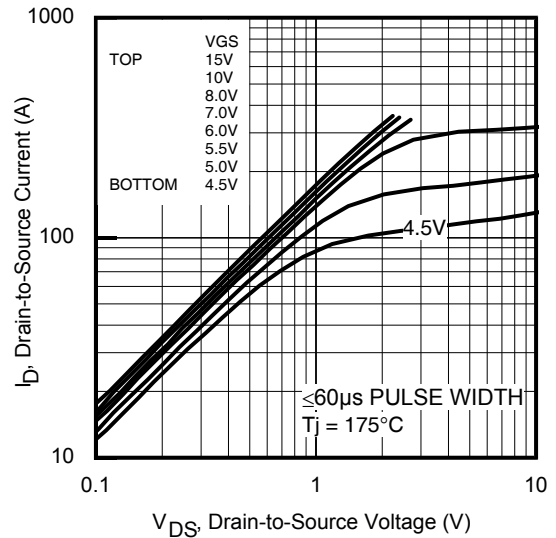
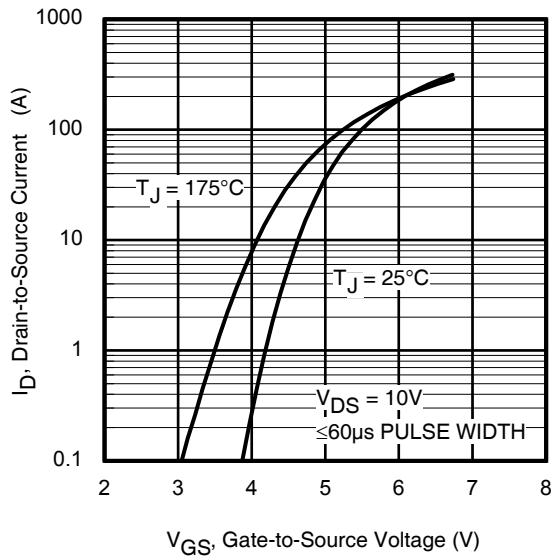
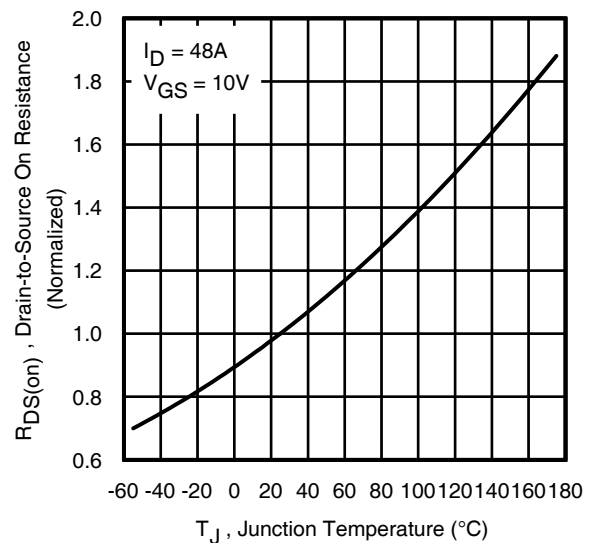
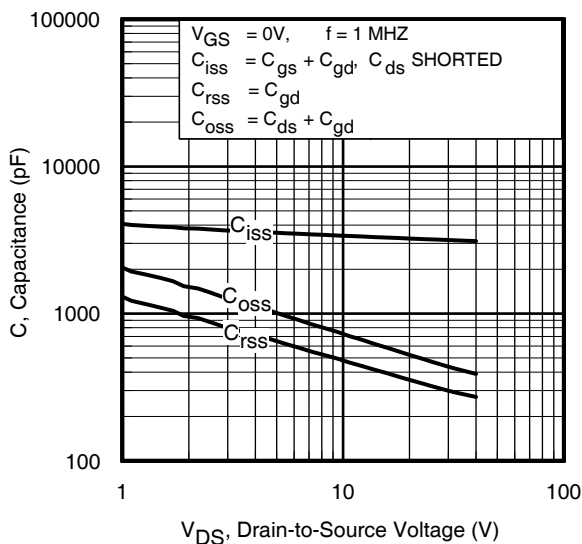
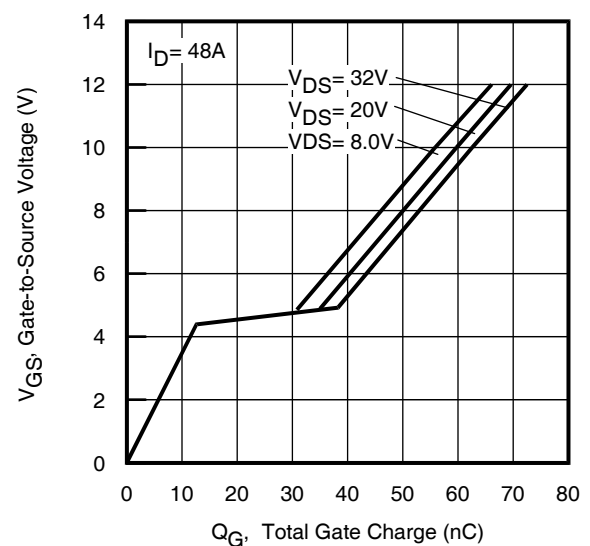
- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Limited by  $T_{Jmax}$ , starting  $T_J = 25^\circ\text{C}$ ,  $L = 270\mu\text{H}$ ,  $R_G = 50\Omega$ ,  $I_{AS} = 48\text{A}$ ,  $V_{GS} = 10\text{V}$ .
- ③  $I_{SD} \leq 48\text{A}$ ,  $di/dt \leq 894\text{A}/\mu\text{s}$ ,  $V_{DD} \leq V_{(BR)DSS}$ ,  $T_J \leq 175^\circ\text{C}$ .
- ④ Pulse width  $\leq 400\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- ⑤  $C_{oss}$  eff. (TR) is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .
- ⑥  $C_{oss}$  eff. (ER) is a fixed capacitance that gives the same energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .
- ⑦  $R_\theta$  is measured at  $T_J$  approximately  $90^\circ\text{C}$ .
- ⑧ This value determined from sample failure population, starting  $T_J = 25^\circ\text{C}$ ,  $L = 270\mu\text{H}$ ,  $R_G = 50\Omega$ ,  $I_{AS} = 48\text{A}$ ,  $V_{GS} = 10\text{V}$ .

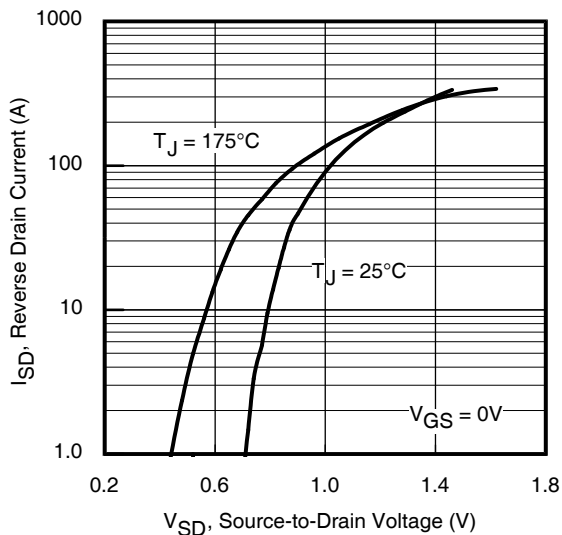
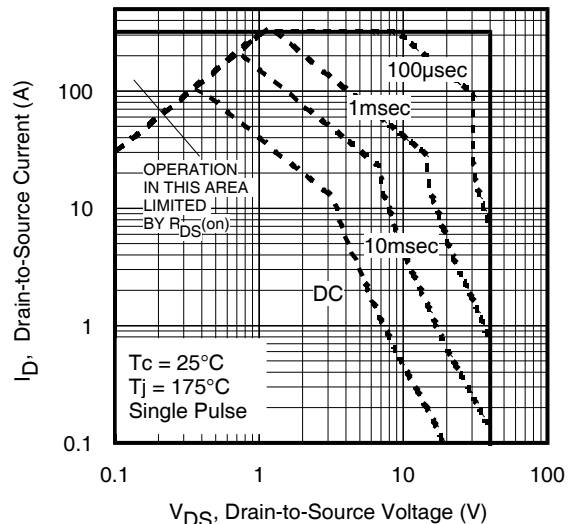
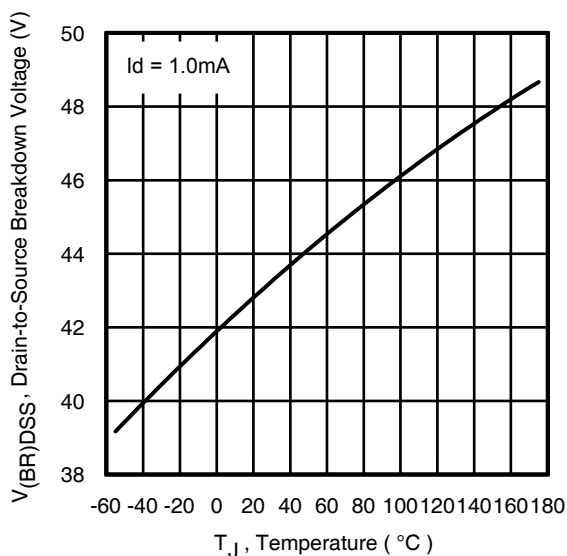
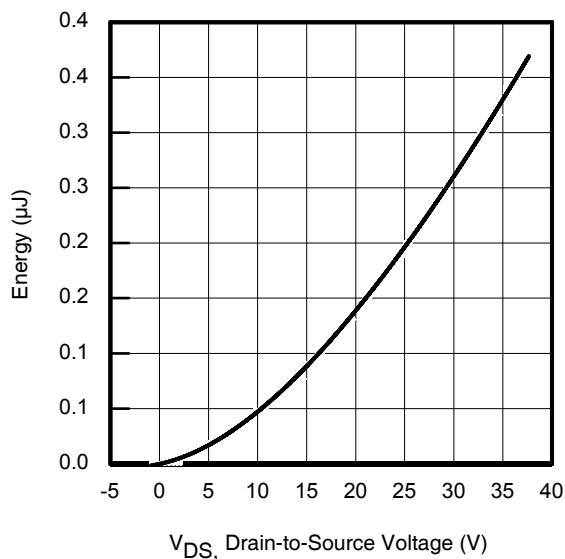
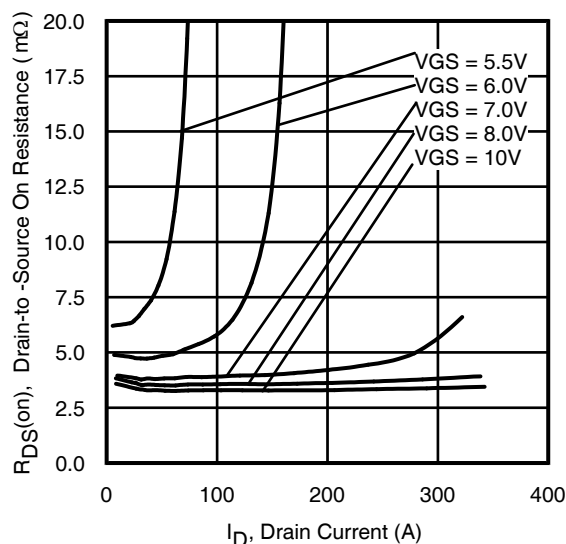
**Dynamic Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)**

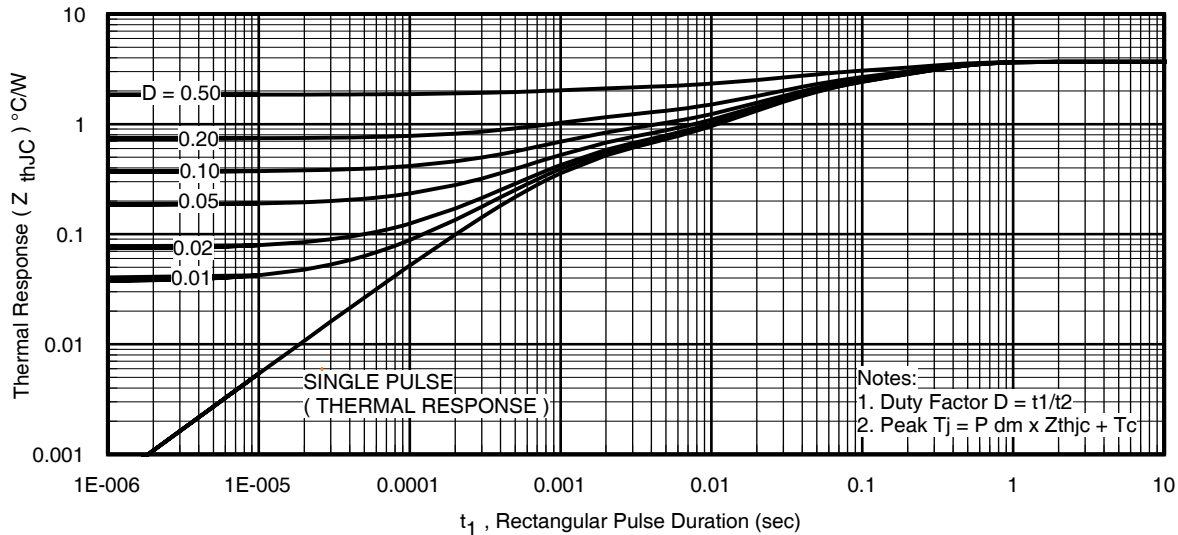
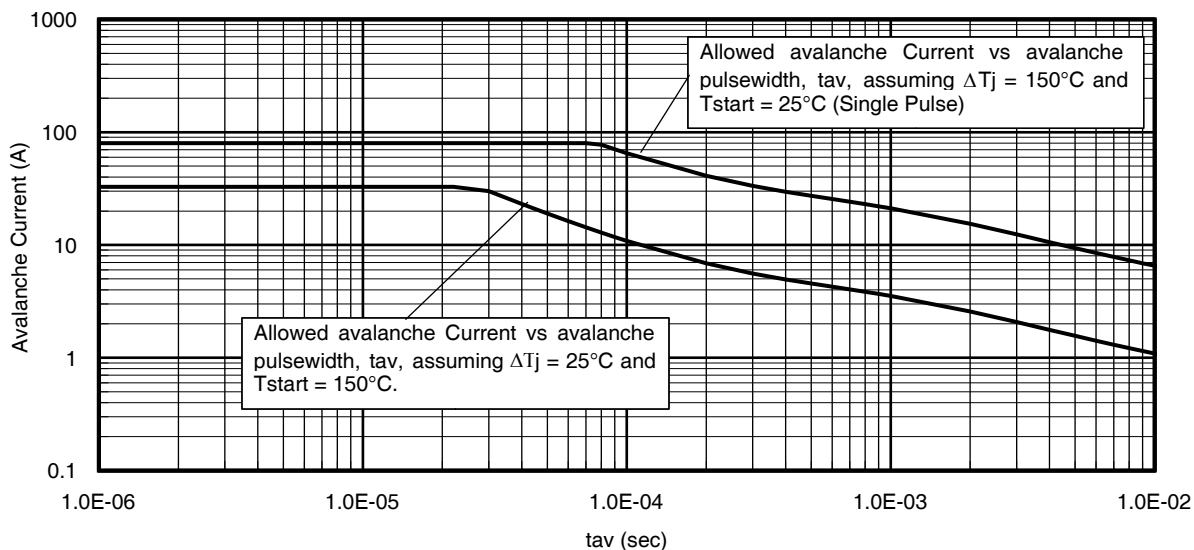
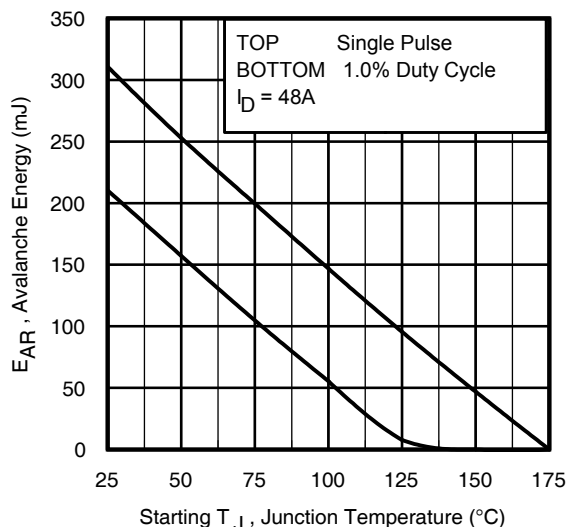
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
gfs	Forward Transconductance	139	—	—	S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 48A
Q <sub>g</sub>	Total Gate Charge	—	60	90	nC	I <sub>D</sub> = 48A V <sub>DS</sub> = 20V V <sub>GS</sub> = 10V
Q <sub>gs</sub>	Gate-to-Source Charge	—	13	—		
Q <sub>gd</sub>	Gate-to-Drain Charge	—	22	—		
Q <sub>sync</sub>	Total Gate Charge Sync. (Q <sub>g</sub> – Q <sub>gd</sub> )	—	38	—		
t <sub>d(on)</sub>	Turn-On Delay Time	—	13	—	ns	V <sub>DD</sub> = 20V I <sub>D</sub> = 48A R <sub>G</sub> = 2.7Ω V <sub>GS</sub> = 10V④
t <sub>r</sub>	Rise Time	—	68	—		
t <sub>d(off)</sub>	Turn-Off Delay Time	—	29	—		
t <sub>f</sub>	Fall Time	—	26	—		
C <sub>iss</sub>	Input Capacitance	—	3199	—	pF	V <sub>GS</sub> = 0V V <sub>DS</sub> = 25V f = 1.0MHz, See Fig.7 V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0V to 32V⑥ V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0V to 32V⑤
C <sub>oss</sub>	Output Capacitance	—	473	—		
C <sub>rss</sub>	Reverse Transfer Capacitance	—	320	—		
C <sub>oss eff.(ER)</sub>	Effective Output Capacitance (Energy Related)	—	561	—		
C <sub>oss eff.(TR)</sub>	Output Capacitance (Time Related)	—	679	—		

**Diode Characteristics**

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>s</sub>	Continuous Source Current (Body Diode)①	—	—	80	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①	—	—	320		
V <sub>SD</sub>	Diode Forward Voltage	—	—	1.3	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 48A, V <sub>GS</sub> = 0V ④
dv/dt	Peak Diode Recovery dv/dt③	—	6.6	—	V/ns	T <sub>J</sub> = 175°C, I <sub>S</sub> = 48A, V <sub>DS</sub> = 40V ③
t <sub>rr</sub>	Reverse Recovery Time	—	28	—	ns	V <sub>DD</sub> = 34V I <sub>F</sub> = 48A, di/dt = 100A/μs ④
		—	29	—		
Q <sub>rr</sub>	Reverse Recovery Charge	—	25	—	nC	T <sub>J</sub> = 25°C T <sub>J</sub> = 125°C
		—	27	—		
I <sub>RRM</sub>	Reverse Recovery Current	—	1.5	—	A	T <sub>J</sub> = 25°C


**Fig 3.** Typical Output Characteristics

**Fig 4.** Typical Output Characteristics

**Fig 5.** Typical Transfer Characteristics

**Fig 6.** Normalized On-Resistance vs. Temperature

**Fig 7.** Typical Capacitance vs. Drain-to-Source Voltage

**Fig 8.** Typical Gate Charge vs. Gate-to-Source Voltage


**Fig 9.** Typical Source-Drain Diode Forward Voltage

**Fig 10.** Maximum Safe Operating Area

**Fig 11.** Drain-to-Source Breakdown Voltage

**Fig 12.** Typical  $C_{oss}$  Stored Energy

**Fig 13.** Typical On-Resistance vs. Drain Current


**Fig 14. Maximum Effective Transient Thermal Impedance, Junction-to-Case**

**Fig 15. Avalanche Current vs. Pulse Width**

**Fig 16. Maximum Avalanche Energy vs. Temperature**
**Notes on Repetitive Avalanche Curves , Figures 15, 16:  
(For further info, see AN-1005 at www.irf.com)**

1. Avalanche failures assumption:  
Purely a thermal phenomenon and failure occurs at a temperature far in excess of  $T_{jmax}$ . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as  $T_{jmax}$  is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 23a, 23b.
4.  $P_{D(ave)}$  = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6.  $I_{av}$  = Allowable avalanche current.
7.  $\Delta T$  = Allowable rise in junction temperature, not to exceed  $T_{jmax}$  (assumed as 25°C in Figure 14, 15).  
 $t_{av}$  = Average time in avalanche.  
 $D$  = Duty cycle in avalanche =  $t_{av} \cdot f$   
 $Z_{thJC}(D, t_{av})$  = Transient thermal resistance, see Figures 13)  
 $P_{D(ave)} = 1/2 ( 1.3 \cdot BV \cdot I_{av} ) = \Delta T / Z_{thJC}$   
 $I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$   
 $E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$

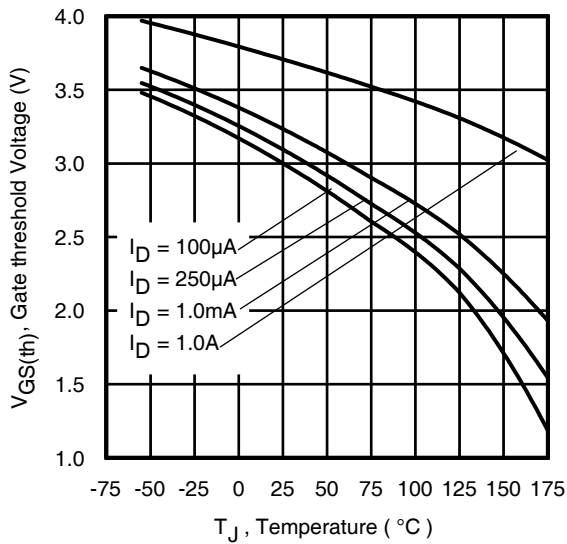


Fig 17. Threshold Voltage vs. Temperature

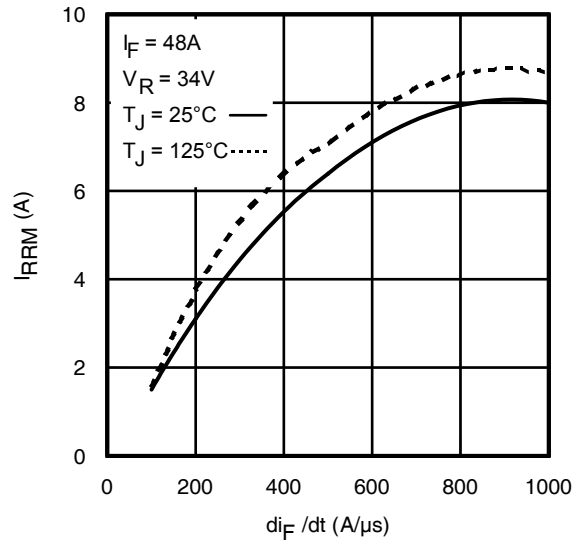


Fig 18. Typical Recovery Current vs.  $di_F/dt$

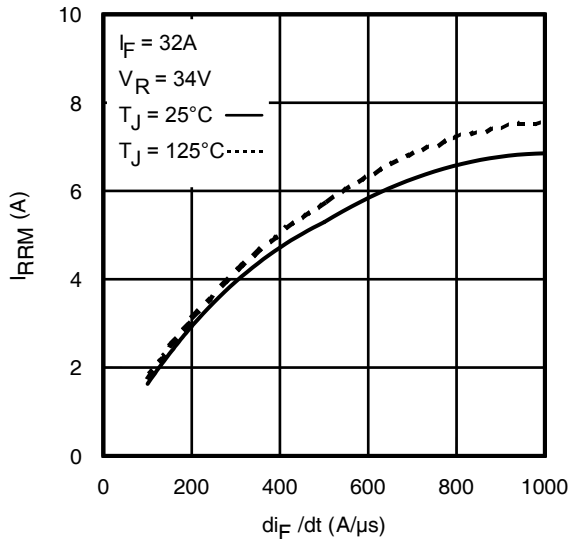


Fig 19. Typical Recovery Current vs.  $di_F/dt$

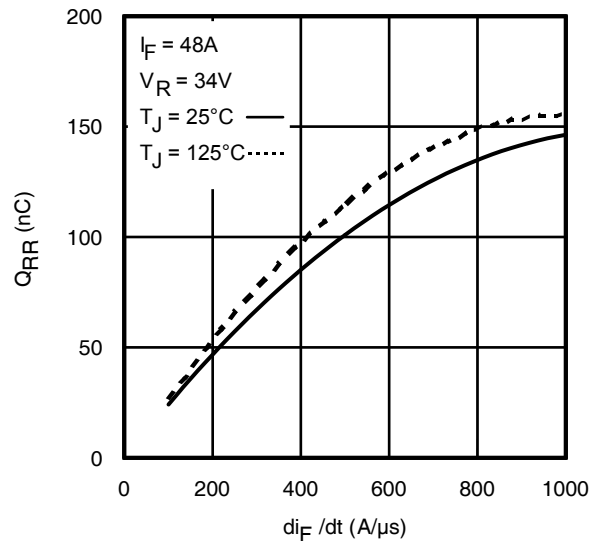


Fig 20. Typical Stored Charge vs.  $di_F/dt$

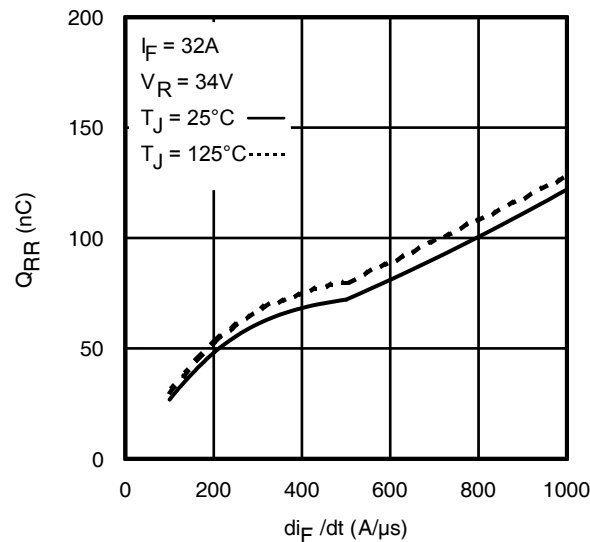
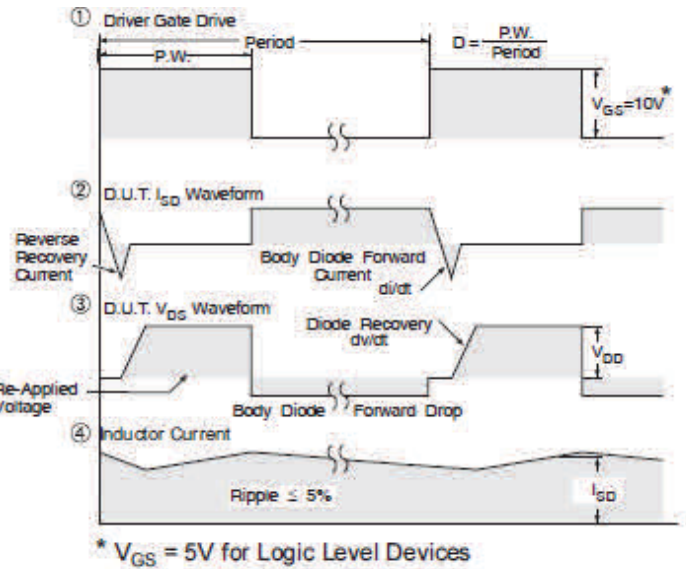
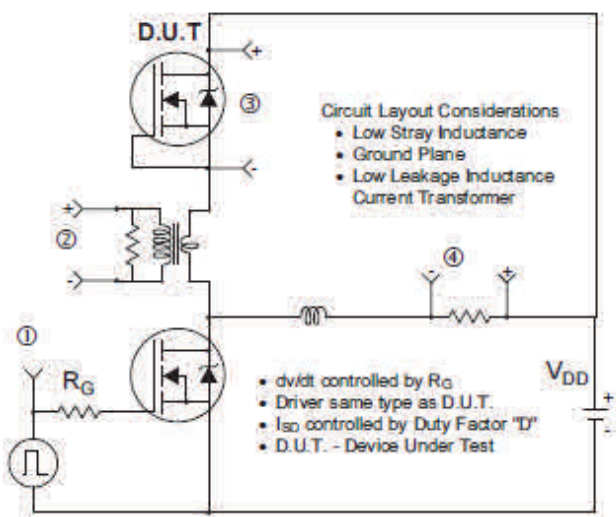
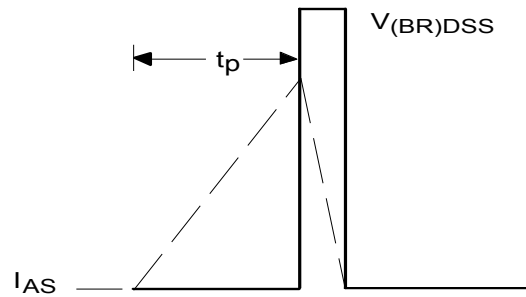


Fig 21. Typical Stored Charge vs.  $di_F/dt$

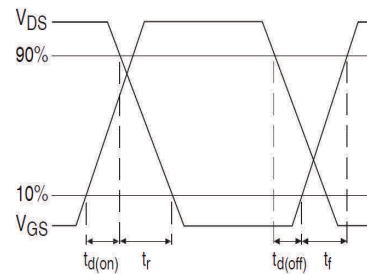


**Fig 22.** Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs



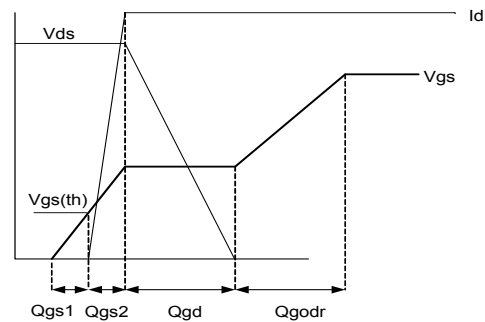
**Fig 23a.** Unclamped Inductive Test Circuit

**Fig 23b.** Unclamped Inductive Waveforms



**Fig 24a.** Switching Time Test Circuit

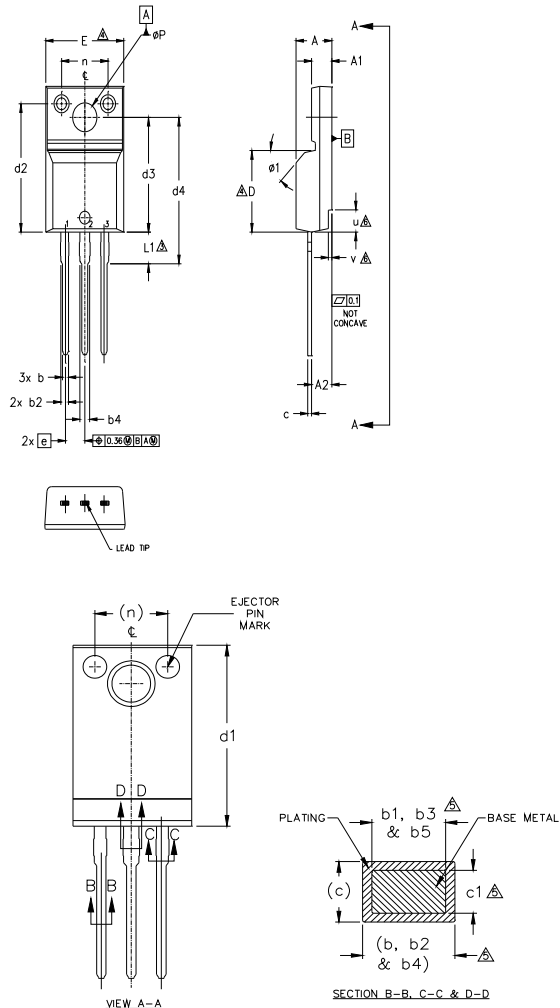
**Fig 24b.** Switching Time Waveforms



**Fig 25a.** Gate Charge Test Circuit

**Fig 25b.** Gate Charge Waveform



**TO-220 Full-Pak Package Outline (Dimensions are shown in millimeters (inches))**

**NOTES:**

- 1.0 DIMENSIONING AND TOLERANCING AS PER ASME Y14.5 M- 1994.
- 2.0 DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
- 3.0 LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
- 4.0 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTER MOST EXTREMES OF THE PLASTIC BODY.
- 5.0 DIMENSION b1, b3, b5 & c1 APPLY TO BASE METAL ONLY.
- 6.0 STEP OPTIONAL ON PLASTIC BODY DEFINED BY DIMENSIONS u & v.
- 7.0 CONTROLLING DIMENSION : INCHES.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.57	4.83	.180	.190	
A1	2.57	2.83	.101	.111	
A2	2.41	2.92	.095	.115	
b	0.62	.094	0.24	.037	
b1	0.62	0.89	.024	0.35	5
b2	0.76	1.27	.030	.050	
b3	0.76	1.22	.030	.048	5
b4	1.02	1.52	.040	.060	
b5	1.02	1.47	.040	.058	5
c	0.33	0.63	.013	.025	
c1	0.33	0.58	.013	.023	5
D	8.65	9.80	.341	.386	4
d1	15.80	16.12	.622	.635	
d2	13.97	14.22	.550	.560	
d3	12.30	12.92	.484	.509	
d4	8.64	9.91	.340	.390	
E	9.63	10.63	.379	.419	4
e	2.54 BSC		.100 BSC		
L	13.20	13.72	.520	.540	
L1	3.10	2.31	.122	.138	3
n	6.05	6.15	.238	.242	
phi P	3.05	3.45	.120	.136	
u	2.40	2.50	.094	.098	6
v	0.40	0.50	.016	.020	6
phi 1	-	45°	-	45°	

**LEAD ASSIGNMENTS**

- HEXFET**
- 1.- GATE
  - 2.- DRAIN
  - 3.- SOURCE

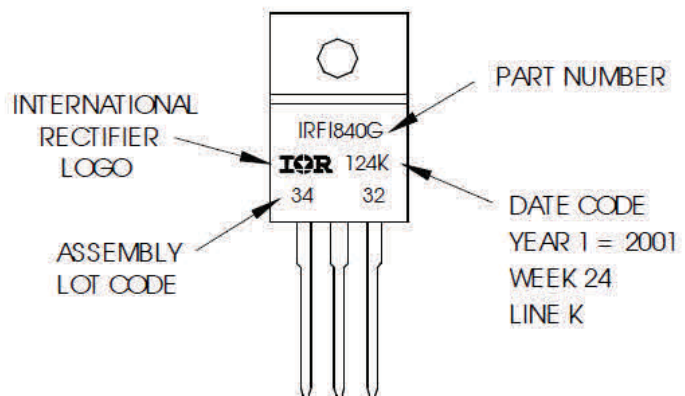
**IGBTs, CoPACK**

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER

**TO-220 Full-Pak Part Marking Information**

EXAMPLE: THIS IS AN IRFI840G  
WITH ASSEMBLY  
LOT CODE 3432  
ASSEMBLED ON WW24, 2001  
IN THE ASSEMBLY LINE "K"

Note: "P" in assembly line position  
indicates "Lead-Free"



TO-220AB Full-Pak packages are not recommended for Surface Mount Application.

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

**Qualification Information†**

<b>Qualification Level</b>	Industrial	
<b>Moisture Sensitivity Level</b>	TO-220 Full-Pak	N/A
<b>RoHS Compliant</b>	Yes	

† Qualification standards can be found at International Rectifier’s web site: <http://www.irf.com/product-info/reliability/>

†† Applicable version of JEDEC standard at the time of product release.

单击下面可查看定价，库存，交付和生命周期等信息

[>>Infineon Technologies\(英飞凌\)](#)